

ABSTRACT

A method of forming and a structure of an integrated circuit are provided. A gate dielectric is formed on a semiconductor substrate, and a gate is formed over a gate dielectric on the semiconductor substrate. Source/drain junctions are formed in the semiconductor
5 substrate. Ultra-uniform silicides are formed on the source/drain junctions, and a dielectric layer is deposited above the semiconductor substrate. Contacts are then formed in the dielectric layer to the ultra-uniform silicides.